

TO-92MOD Plastic-Encapsulate Transistors

2SA966 TRANSISTOR (PNP)

FEATURE

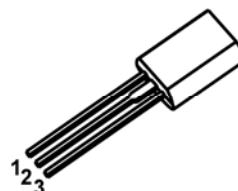
- Complementary to 2SC2236 and 3 Watts output Applications.

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1.5	A
P _c	Collector Power Dissipation	0.9	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C = -1mA, I _E =0	-30			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = -10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = -1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -30V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C = -500mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -1.5 A, I _B = -0.03A			-2	V
Base-emitter voltage	V _{BE}	I _C = -500mA, V _{CE} =-2V			-1	V
Transition frequency	f _T	V _{CE} = -2V, I _C =-500mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320